

Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

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Complete if Known

<b>Application Number</b>	10/634174
<b>Filing Date</b>	August 5, 2003
<b>First Named Inventor</b>	Forbes, Leonard
<b>Group Art Unit</b>	2826 2823
<b>Examiner Name</b>	Tran, Tan J. Garcia

Sheet 1 of 7

Attorney Docket No: 1303.102US1

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Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

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		Examiner Name	Tran, Tan J. Garcia			
Sheet 2 of 7		Attorney Docket No: 1303.102US1				

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\* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 600. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

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EXAMINER

*Juanita Garcia*

DATE CONSIDERED

*July 22, 2004*

\* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. <sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached.

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*Joannine J. Garcia*

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EXAMINER

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DATE CONSIDERED

*July 22 2004*